

CMOS Compatible SOI MESFETs for Radiation Hardened DC-to-DC Converters, Phase I

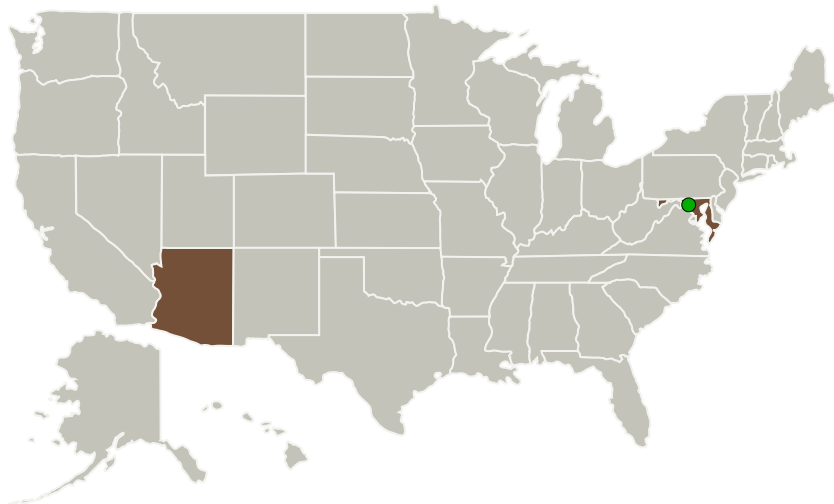
Completed Technology Project (2011 - 2011)



Project Introduction

We have developed a novel metal-semiconductor field-effect-transistor (MESFET) technology suitable for extreme environment electronics. The MESFET technology is fully CMOS-compatible and can be integrated alongside conventional MOSFETs with no changes to the process flow. Unlike the MOSFETs however, the MESFETs do not require a fragile metal-oxide-semiconductor (MOS) interface and are extremely robust. With breakdown voltages in the range 10-50V the MESFET operating voltage greatly exceeds that of the accompanying CMOS. The combination of CMOS compatibility with high breakdown voltage allows for integrated DC-to-DC power conversion solutions that would otherwise require discrete components based on laterally diffused metal-oxide-semiconductor (LDMOS) devices. The MESFETs are intrinsically radiation tolerant up to 1 Mrad(Si) and have been demonstrated to work over the temperature range -196C to +150C. The Phase 1 R&D we are proposing will characterize the large signal switching performance of the SOI MESFETs for buck converter applications in extreme environments.

Primary U.S. Work Locations and Key Partners



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Table of Contents

Project Introduction	1
Primary U.S. Work Locations and Key Partners	1
Project Transitions	2
Organizational Responsibility	2
Project Management	2
Technology Maturity (TRL)	2
Technology Areas	3
Target Destinations	3

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Organizations Performing Work	Role	Type	Location
SJT Micropower	Lead Organization	Industry	Fountain Hills, Arizona
● Goddard Space Flight Center(GSFC)	Supporting Organization	NASA Center	Greenbelt, Maryland

Primary U.S. Work Locations	
Arizona	Maryland

Project Transitions

▶ **February 2011:** Project Start

✓ **August 2011:** Closed out

Closeout Documentation:

- Final Summary Chart(<https://techport.nasa.gov/file/138040>)

Organizational Responsibility

Responsible Mission Directorate:

Space Technology Mission Directorate (STMD)

Lead Organization:

SJT Micropower

Responsible Program:

Small Business Innovation Research/Small Business Tech Transfer

Project Management

Program Director:

Jason L Kessler

Program Manager:

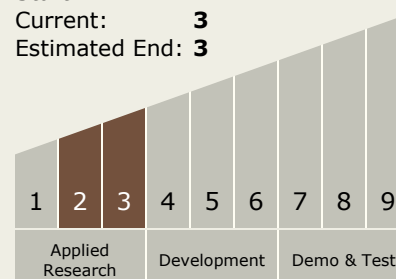
Carlos Torrez

Principal Investigator:

William J Lepkowski

Technology Maturity (TRL)

Start: 2
Current: 3
Estimated End: 3



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Technology Areas

Primary:

- TX10 Autonomous Systems
 - └ TX10.1 Situational and Self Awareness
 - └ TX10.1.4 Hazard Assessment

Target Destinations

The Sun, Earth, The Moon, Mars, Others Inside the Solar System, Outside the Solar System